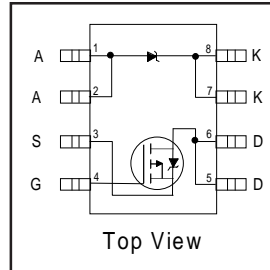


# IRF7326D2

## FETKY™ MOSFET / Schottky Diode

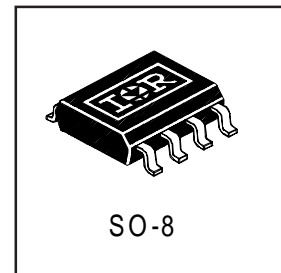
- Co-packaged HEXFET® Power MOSFET and Schottky Diode
- Ideal For Buck Regulator Applications
- P-Channel HEXFET
- Low  $V_F$  Schottky Rectifier
- Generation 5 Technology
- SO-8 Footprint



$V_{DSS} = -30V$
$R_{DS(on)} = 0.10\Omega$
Schottky $V_f = 0.52V$

### Description

The **FETKY** family of co-packaged MOSFETs and Schottky diodes offers the designer an innovative, board space saving solution for switching regulator and power management applications. Generation 5 HEXFET Power MOSFETs utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. Combining this technology with International Rectifier's low forward drop Schottky rectifiers results in an extremely efficient device suitable for use in a wide variety of portable electronics applications.



The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics. The SO-8 package is designed for vapor phase, infrared or wave soldering techniques.

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter		Maximum	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ④	-3.6	A
$I_D @ T_A = 70^\circ C$		-2.9	
$I_{DM}$		-29	
$P_D @ T_A = 25^\circ C$	Power Dissipation ④	2.0	W
$P_D @ T_A = 70^\circ C$		1.3	
	Linear Derating Factor	16	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
dv/dt	Peak Diode Recovery dv/dt ②	-5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +150	°C

### Thermal Resistance Ratings

Parameter		Maximum	Units
$R_{\theta JA}$	Junction-to-Ambient ④	62.5	°C/W

#### Notes:

- ① Repetitive rating; pulse width limited by maximum junction temperature (see figure 9)
- ②  $I_{SD} \leq -1.8A$ ,  $di/dt \leq -90A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ C$
- ③ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$
- ④ Surface mounted on FR-4 board,  $t \leq 10sec$ .

**MOSFET Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Parameter		Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	0.073	0.10	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -1.8A ③
		—	0.13	0.16		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	-1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	2.5	—	—	S	V <sub>DS</sub> = -24V, I <sub>D</sub> = -1.8A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	—	25	nC	I <sub>D</sub> = -1.8A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	2.9		V <sub>DS</sub> = -24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	9.0		V <sub>GS</sub> = -10V (see figure 6) ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	11	—	ns	V <sub>DD</sub> = -15V
t <sub>r</sub>	Rise Time	—	17	—		I <sub>D</sub> = -1.8A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	25	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	18	—		R <sub>D</sub> = 8.2Ω ③
C <sub>iss</sub>	Input Capacitance	—	440	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	200	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	93	—		f = 1.0MHz (see figure 5)

**MOSFET Source-Drain Ratings and Characteristics**

Parameter		Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-2.5	A	
I <sub>SM</sub>	Pulsed Source Current (Body Diode)	—	—	-29		
V <sub>SD</sub>	Body Diode Forward Voltage	—	—	-1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.8A, V <sub>GS</sub> = 0V
t <sub>rr</sub>	Reverse Recovery Time (Body Diode)	—	53	80	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.8A
Q <sub>rr</sub>	Reverse Recovery Charge	—	66	99	nC	di/dt = 100A/μs ③

**Schottky Diode Maximum Ratings**

	Parameter	Max.	Units	Conditions
I <sub>f(av)</sub>	Max. Average Forward Current	2.8	A	50% Duty Cycle. Rectangular Wave, T <sub>c</sub> = 25°C
		1.8		50% Duty Cycle. Rectangular Wave, T <sub>c</sub> = 70°C
I <sub>SM</sub>	Max. peak one cycle Non-repetitive Surge current	200	A	5μs sine or 3μs Rect. pulse
		20		10ms sine or 6ms Rect. pulse
				Following any rated load condition & with V <sub>rrm</sub> applied

**Schottky Diode Electrical Specifications**

	Parameter	Max.	Units	Conditions
V <sub>fm</sub>	Max. Forward voltage drop	0.57	V	I <sub>f</sub> = 3.0, T <sub>J</sub> = 25°C
		0.77		I <sub>f</sub> = 6.0, T <sub>J</sub> = 25°C
		0.52		I <sub>f</sub> = 3.0, T <sub>J</sub> = 125°C
		0.79		I <sub>f</sub> = 6.0, T <sub>J</sub> = 125°C
I <sub>rm</sub>	Max. Reverse Leakage current	0.30	mA	V <sub>r</sub> = 30V, T <sub>J</sub> = 25°C
		37		T <sub>J</sub> = 125°C
C <sub>t</sub>	Max. Junction Capacitance	310	pF	V <sub>r</sub> = 5Vdc ( 100kHz to 1 MHz) 25°C
dv/dt	Max. Voltage Rate of Charge	4900	V/μs	Rated V <sub>r</sub>

( HEXFET is the reg. TM for International Rectifier Power MOSFET's )

Power Mosfet Characteristics

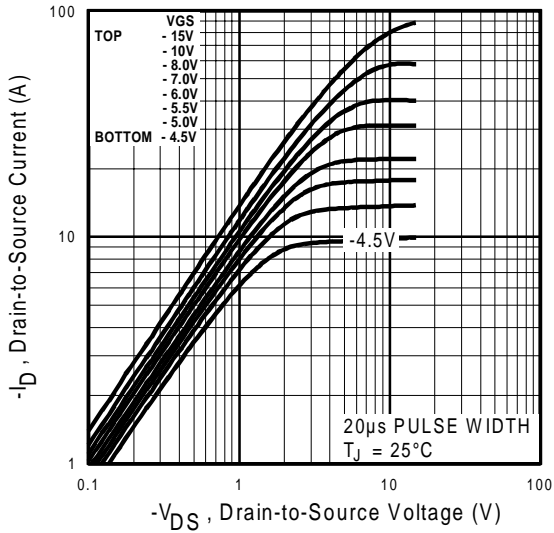


Fig 1. Typical Output Characteristics

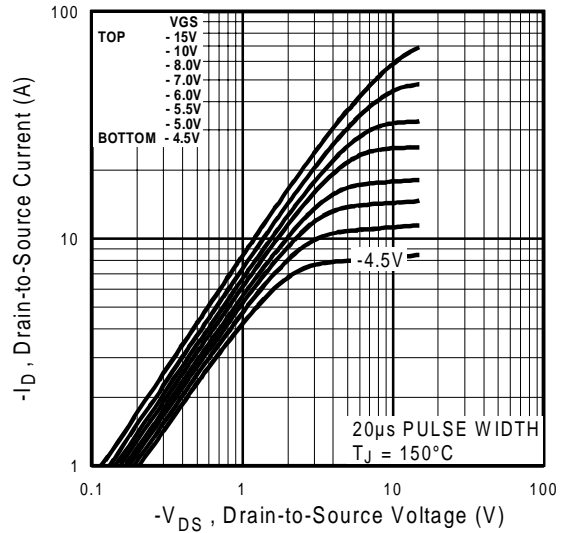


Fig 2. Typical Output Characteristics

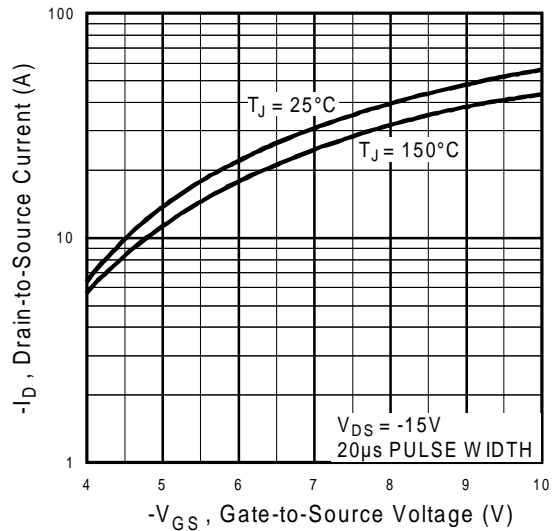


Fig 3. Typical Transfer Characteristics

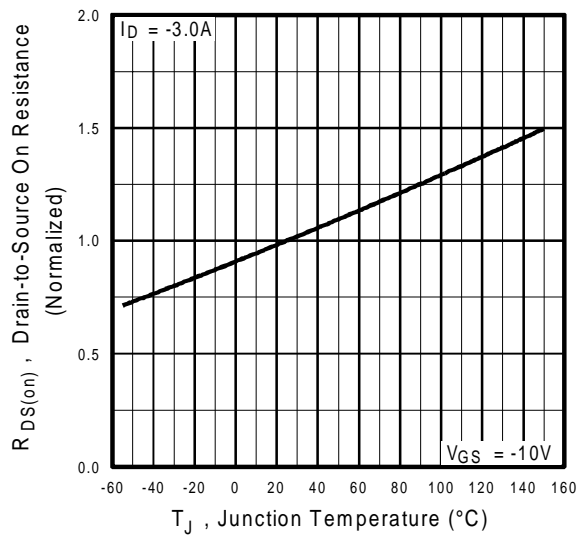
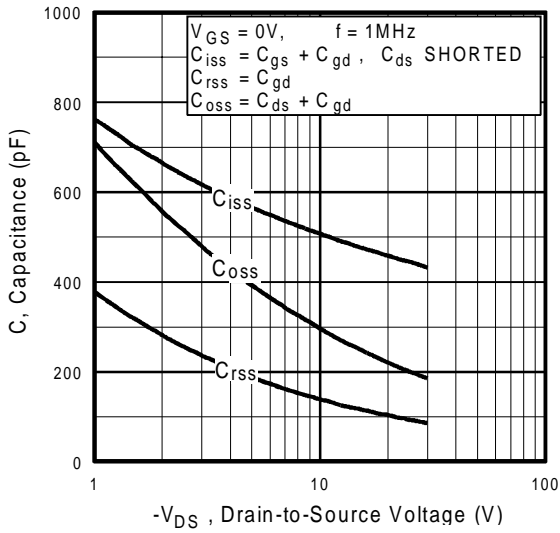
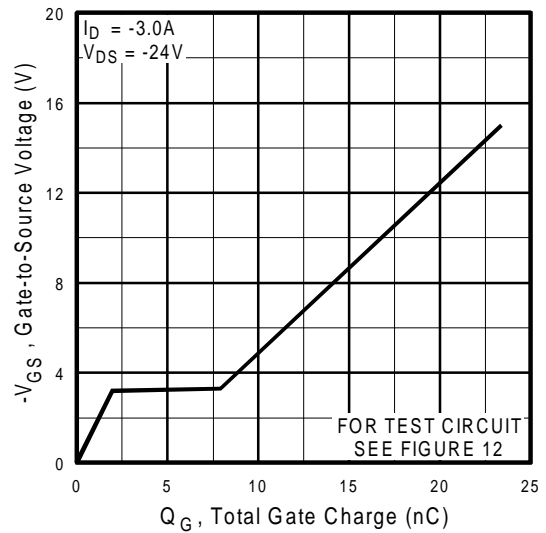


Fig 4. Normalized On-Resistance Vs. Temperature

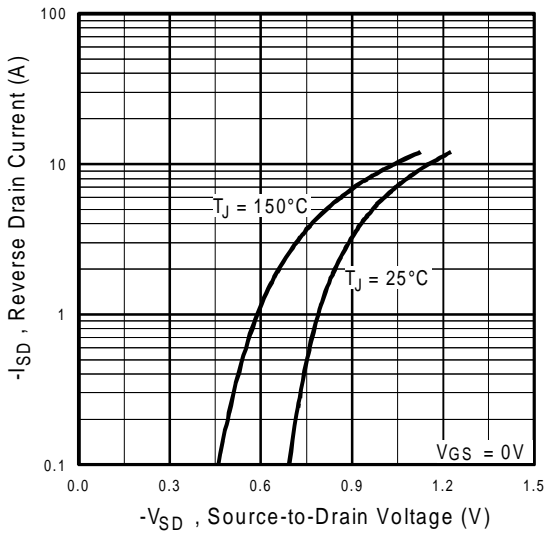
Power Mosfet Characteristics



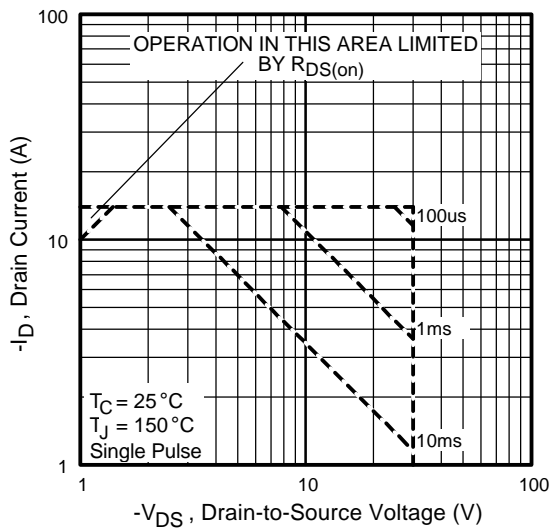
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

Power Mosfet Characteristics

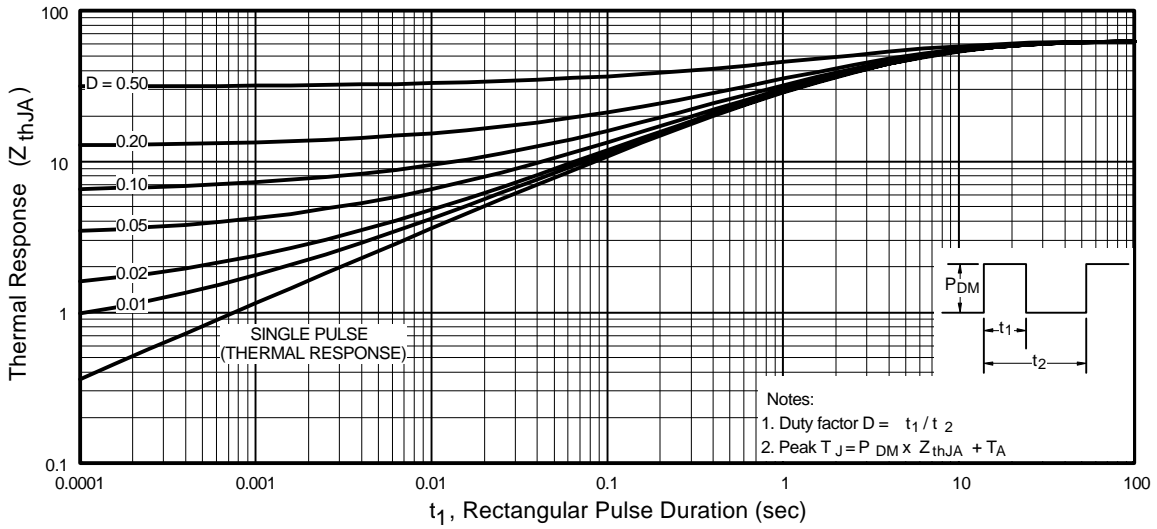


Fig 9. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

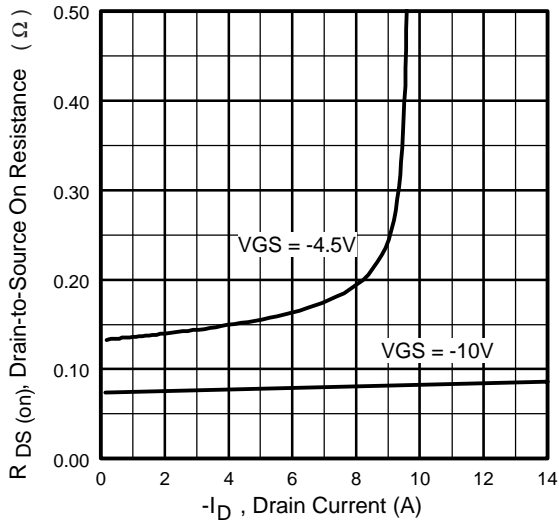


Fig 10. Typical On-Resistance Vs. Drain Current

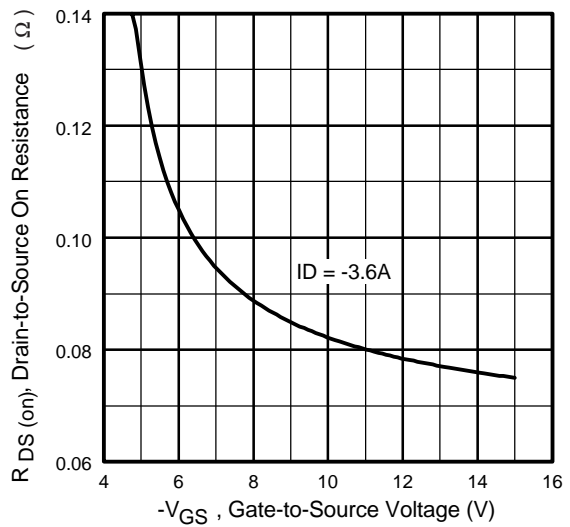
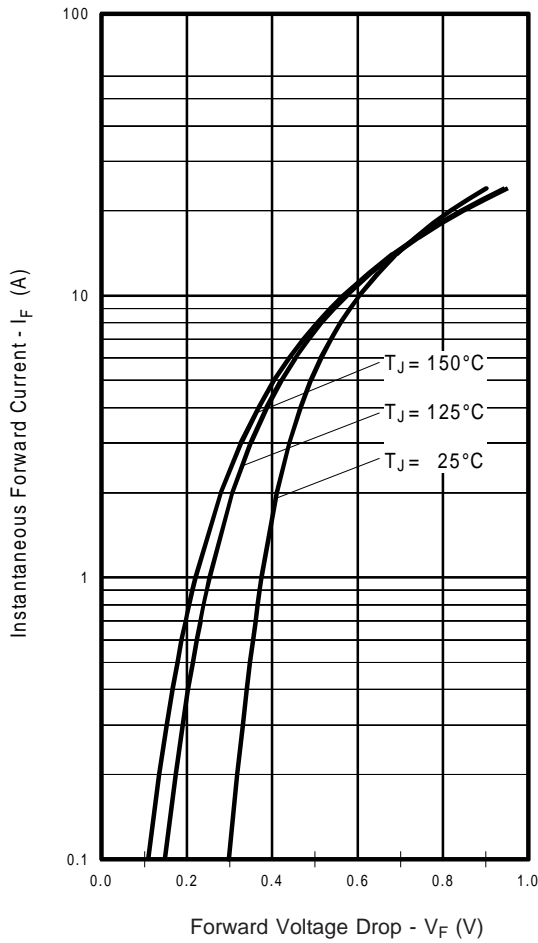
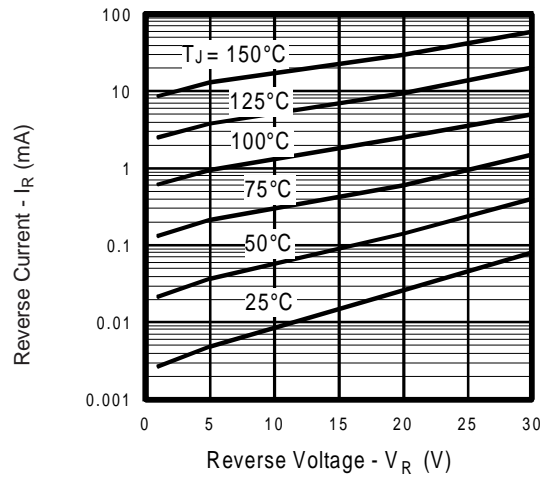


Fig 11. Typical On-Resistance Vs. Gate Voltage

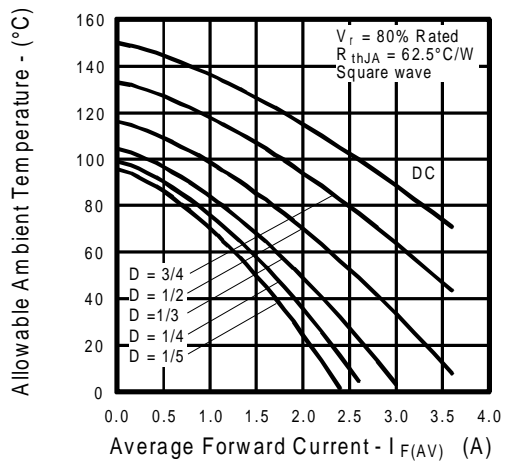
Schottky Diode Characteristics



**Fig. 12** - Typical Forward Voltage Drop Characteristics

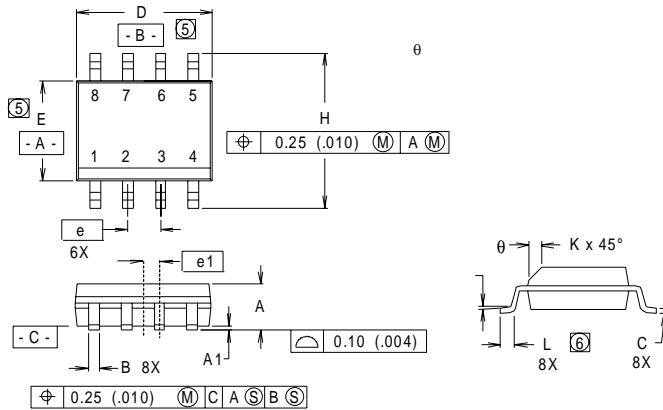


**Fig. 13** - Typical Values of Reverse Current Vs. Reverse Voltage



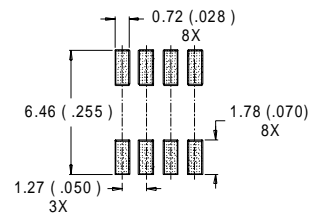
**Fig.14** - Maximum Allowable Ambient Temp. Vs. Forward Current

**SO-8 Package Details**



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
$\theta$	0°	8°	0°	8°

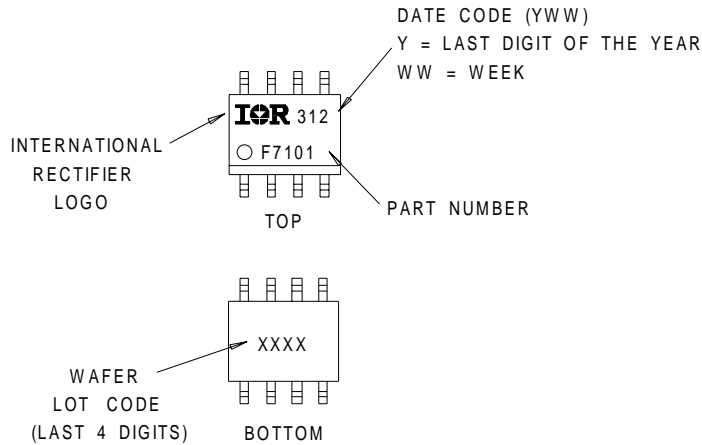
**RECOMMENDED FOOTPRINT**



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS  
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

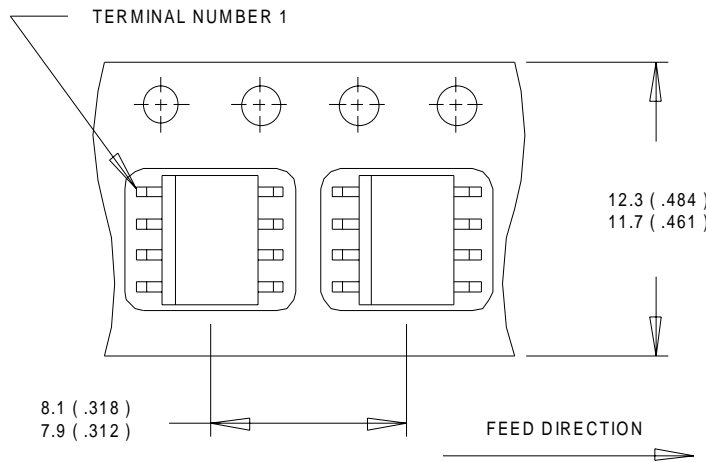
**Part Marking  
 (IRF7101 example )**



# IRF7326D2

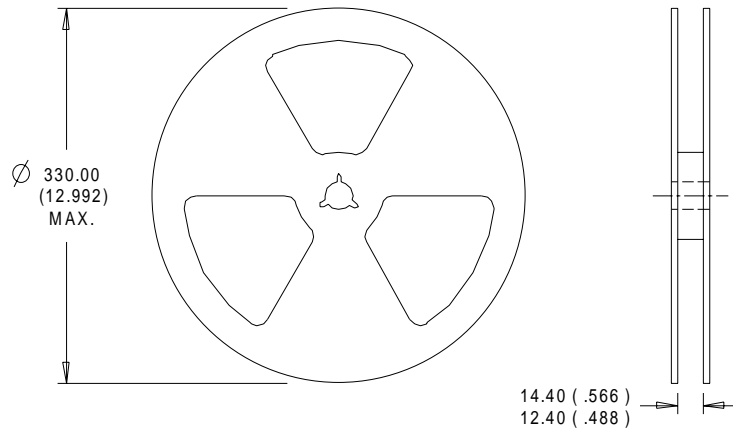
Tape and Reel

International  
**IR** Rectifier



**NOTES:**

- 1. CONTROLLING DIMENSION : MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

- 1. CONTROLLING DIMENSION : MILLIMETER.
- 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International  
**IR** Rectifier

**WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

**IR GREAT BRITAIN:** Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

**IR FAR EAST:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630

**IR TAIWAN:** 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

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